

(c) forming a gate electrode through a gate oxide film on said surface of said silicon layer in said first region, said gate electrode extending on said partial oxide film in said second region;

(d) introducing a first impurity of a second conductivity type into both ends of said gate electrode in said first region using a first mask layer covering said third region and exposing said first region; and

(e) introducing a second impurity of said first conductivity type into said third region using a second mask layer covering said first region and exposing said third region, wherein  
*Said partial oxide film and*  
said first mask layer covers said partial oxide film and a part of said gate electrode in said second region.

*3/21/2006*  
*WL*

30. (New) The method of manufacturing a semiconductor device according to claim 29, wherein

said silicon layer includes a fourth region of said second conductivity type different from said first, second and third regions,

in said step (d), said first mask layer covers said fourth region,

in said step (e), said second mask layer exposes said fourth region, and

said second impurity is introduced into said fourth region.